

SN74LV14B-EP Enhanced Product, 2-V to 5.5-V, Low-Noise, Hex Schmitt-Trigger Inverters

1 Features

- 2 V to 5.5 V V_{CC} operation
- Maximum t_{pd} of 14 ns at 5 V
- Supports mixed-mode voltage operation on all ports
- I_{off} supports partial-power-down mode operation
- Latch-up performance exceeds 250 mA per JESD 17
- Operating ambient temperature: -55°C to +125°C
- Supports defense, aerospace, and medical applications:
 - Controlled baseline
 - One assembly and test site
 - One fabrication site
 - Extended product life cycle
 - Product traceability

2 Applications

- [Synchronize inverted clock inputs](#)
- [Debounce a switch](#)
- Invert a digital signal

3 Description

The SN74LV14B-EP device contains six independent Inverter with Schmitt-trigger inputs designed for 2 V to 5.5 V V_{CC} operation. Each gate performs the Boolean function $Y = \bar{A}$ in positive logic.

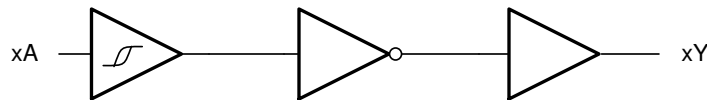
This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾
SN74LV14B-EP	PW (TSSOP, 14)	5 mm × 6.4 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

(2) The package size (length × width) is a nominal value and includes pins, where applicable.



Logic Diagram (Positive Logic)



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4 Revision History

DATE	REVISION	NOTES
August 2023	*	Initial Release

5 Pin Configuration and Functions

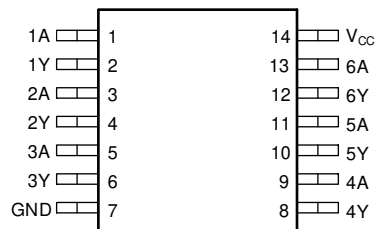


Figure 5-1. SN74LV14B-EP: PW Package, 14-Pin TSSOP (Top View)

Table 5-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
1A	1	I	Channel 1, Input
1Y	2	O	Channel 1 ,output
2A	3	I	Channel 2, Input
2Y	4	O	Channel 2 ,output
3A	5	I	Channel 3, Input
3Y	6	O	Channel 3 ,output
GND	7	G	Ground
4Y	8	O	Channel 4 ,output
4A	9	I	Channel 4 ,input
5Y	10	O	Channel 5 ,output
5A	11	I	Channel 5 ,input
6Y	12	O	Channel 6 ,output
6A	13	I	Channel 6 ,input
V _{CC}	14	P	Positive supply

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.

6 Specifications

6.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	-0.5	7	V
V _I	Input voltage ⁽²⁾	-0.5	7	V
V _O	Voltage range applied to any output in the high-impedance or power-off state ⁽²⁾	-0.5	7	V
V _O	Output voltage ⁽²⁾ ⁽³⁾	-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-20 mA
I _{OK}	Output clamp current	V _O < 0		-50 mA
I _O	Continuous output current	V _O = 0 to V _{CC}		±25 mA
	Continuous current through V _{CC} or GND			±50 mA
T _{stg}	Storage temperature	-65	150	°C

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. *Absolute Maximum Ratings* do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If used outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) This value is limited to 5.5 V maximum.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
		Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	2	5.5	V
V _{IH}	High-level input voltage	V _{CC} = 2 V	1.5	V
		V _{CC} = 2.3 V to 5.5 V	V _{CC} × 0.7	
V _{IL}	Low-level input voltage	V _{CC} = 2 V	0.5	V
		V _{CC} = 2.3 V to 5.5 V	V _{CC} × 0.3	
V _I	Input voltage	0	5.5	V
V _O	Output voltage	0	V _{CC}	V
I _{OH}	High-level output current	V _{CC} = 2 V	-50	μA
		V _{CC} = 2.3 V to 2.7 V	-2	
		V _{CC} = 3 V to 3.6 V	-6	
		V _{CC} = 4.5 V to 5.5 V	-12	
I _{OL}	Low-level output current	V _{CC} = 2 V	50	μA
		V _{CC} = 2.3 V to 2.7 V	2	
		V _{CC} = 3 V to 3.6 V	6	
		V _{CC} = 4.5 V to 5.5 V	12	
T _A	Operating free-air temperature	-55	125	°C

- (1) All unused inputs of the device must be held at V_{CC} or GND for proper device operation. See [Implications of Slow or Floating CMOS Inputs](#).

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74LV14B-EP	UNIT
		PW (TSSOP)	
		14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	151	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	80	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	94.2	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	28	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	93.6	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	—	°C/W

(1) For more information about traditional and new thermal metrics, see [Semiconductor and IC Package Thermal Metrics](#).

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted).

PARAMETER		V_{CC}	MIN	TYP	MAX	UNIT
V_{T+}	Positive-going threshold	2.5 V			1.78	V
		3.3 V			2.31	
		5 V			3.5	
V_{T-}	Negative-going threshold	2.5 V	0.75			V
		3.3 V	0.97			
		5 V	1.5			
ΔV_T	Hysteresis ($V_{T+} - V_{T-}$)	2.5 V	0.25		1	V
		3.3 V	0.33		1.37	
		5 V	0.5		2	
V_{OH}	$I_{OH} = -50$ mA	2 V to 5.5 V	$V_{CC} - 0.1$			V
	$I_{OH} = -2$ mA	2.3 V	2			
	$I_{OH} = -6$ mA	3 V	2.48			
	$I_{OH} = -12$ mA	4.5 V	3.8			
V_{OL}	$I_{OL} = 50$ mA	2 V to 5.5 V			0.1	V
	$I_{OL} = 2$ mA	2.3 V			0.4	
	$I_{OL} = 6$ mA	3 V			0.44	
	$I_{OL} = 12$ mA	4.5 V			0.55	
I_I	$V_I = 5.5$ V or GND	0 V to 5.5 V			± 1	μ A
I_{CC}	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			20	μ A
I_{off}	V_I or $V_O = 0$ to 5.5 V	0 V			5	μ A
C_i	$V_I = V_{CC}$ or GND	3.3 V		2.3		pF

6.6 Switching Characteristics, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$

over operating free-air temperature range (unless otherwise noted), (see [Figure 7-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAP	25°C			-55°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
t_{pd}	A	Y	$C_L = 50\text{ pF}$		9.6	16.3	1		20.4	ns

6.7 Switching Characteristics, $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted), (see [Figure 7-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAP	25°C			-55°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
t_{pd}	A	Y	$C_L = 50\text{ pF}$		6.7	10.6	1		14	ns

6.8 Noise Characteristics

$V_{CC} = 3.3\text{ V}$, $C_L = 50\text{ pF}$, $T_A = 25^\circ\text{C}^{(1)}$

		SN74LV14A			UNIT
		MIN	TYP	MAX	
$V_{OL(P)}$	Quiet output, maximum dynamic		0.2	0.8	V
$V_{OL(V)}$	Quiet output, minimum dynamic		-0.1	-0.8	V
$V_{OH(V)}$	Quiet output, minimum dynamic		3.1		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

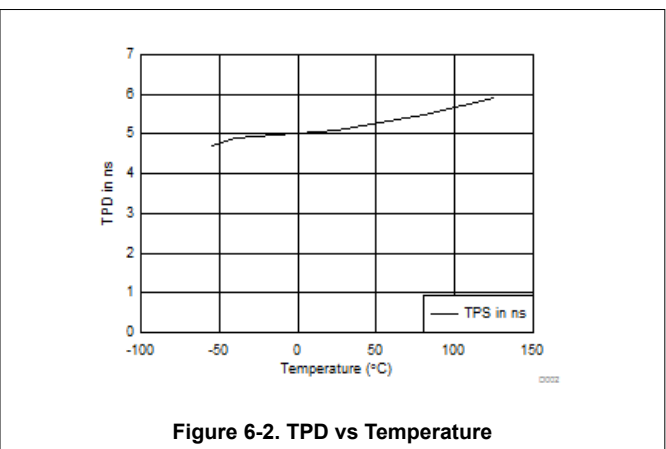
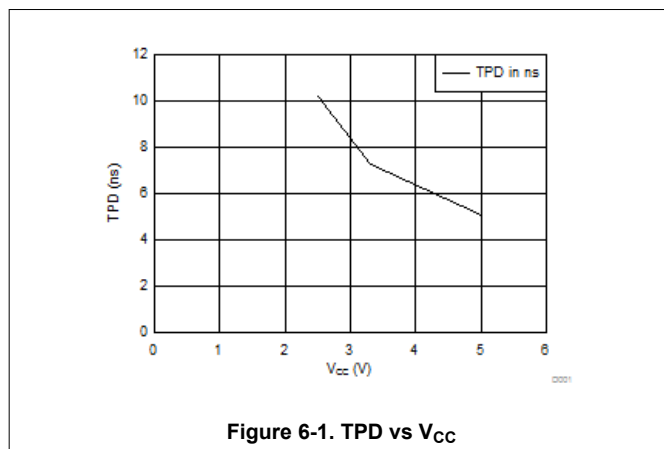
(1) Characteristics are for surface-mount packages only.

6.9 Operating Characteristics

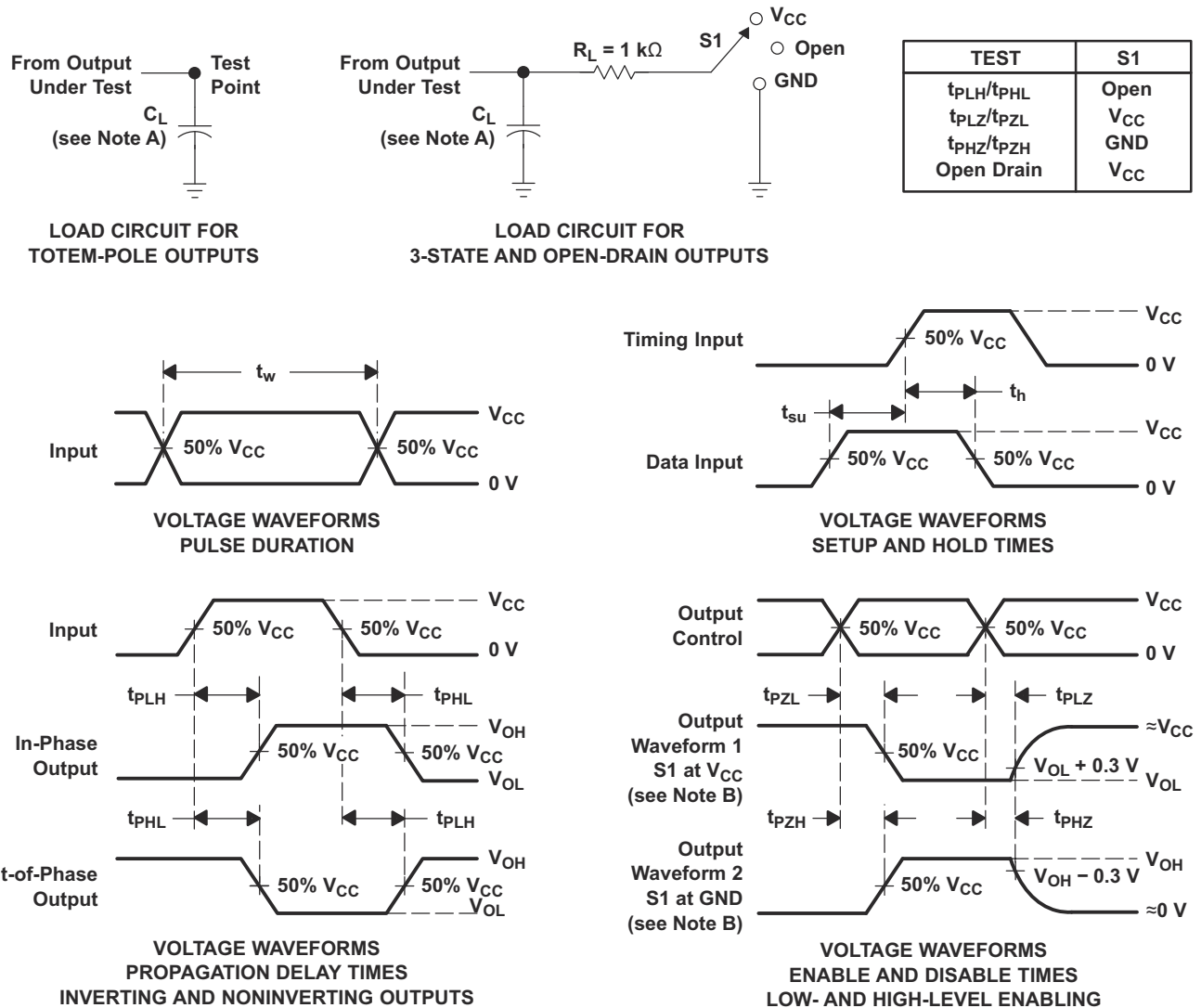
$T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	$C_L = 50\text{ pF}$ $f = 10\text{ MHz}$	3.3 V	8.8	pF
			5 V	9.6	

6.10 Typical Characteristics



7 Parameter Measurement Information



- A. C_L includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1$ MHz, $Z_O = 50 \Omega$, $t_r \leq 3$ ns, and $t_f \leq 3$ ns.
- D. The outputs are measured one at a time, with one input transition per measurement.
- E. t_{PZL} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PHL} and t_{PLH} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 7-1. Load Circuit and Voltage Waveforms

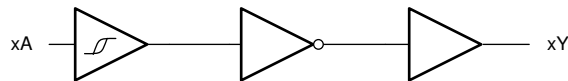
8 Detailed Description

8.1 Overview

The SN74LV14B-EP device contains six independent Inverter with Schmitt-trigger inputs designed for 2 V to 5.5 V V_{CC} operation. Each gate performs the Boolean function $Y = \bar{A}$ in positive logic.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 CMOS Schmitt-Trigger Inputs

This device includes inputs with the Schmitt-trigger architecture. These inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics* table from the input to ground. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings* table, and the maximum input leakage current, given in the *Electrical Characteristics* table, using Ohm's law ($R = V \div I$).

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the *Electrical Characteristics* table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs with slow transitioning signals will increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see [Understanding Schmitt Triggers](#).

8.3.2 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

8.3.3 Partial Power Down (I_{off})

This device includes circuitry to disable all outputs when the supply pin is held at 0 V. When disabled, the outputs will neither source nor sink current, regardless of the input voltages applied. The amount of leakage current at each output is defined by the I_{off} specification in the *Electrical Characteristics* table.

8.3.4 Clamp Diode Structure

Figure 8-1 shows the inputs and outputs to this device have negative clamping diodes only.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

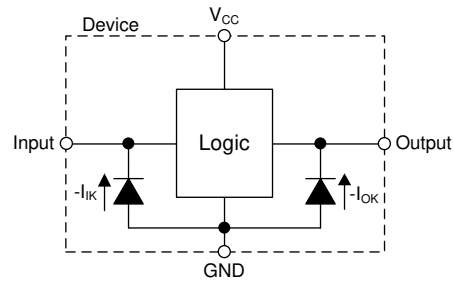


Figure 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

**Table 8-1. Function Table
(Each Inverter)**

INPUT ⁽¹⁾ A	OUTPUT ⁽²⁾ Y
H	L
L	H

- (1) H = High Voltage Level, L = Low Voltage Level, X = Do not Care
 (2) H = Driving High, L = Driving Low, Z = High Impedance State

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The SN74LV14B-EP can be used to add an additional stage to a counter with an external flip-flop. Because counters use a negative edge trigger, the flip-flop's clock input must be inverted to provide this function. Having Schmitt-trigger inputs is important in this application to eliminate any noise issues that could impact the counting function which could lead to incorrect frequency division. This function only requires one of the six available inverters in the SN74LV14B-EP device, so the remaining channels can be used for other applications needing an inverted signal or improved signal integrity. Unused inputs must be terminated at V_{CC} or GND. Unused outputs can be left floating.

9.2 Typical Application

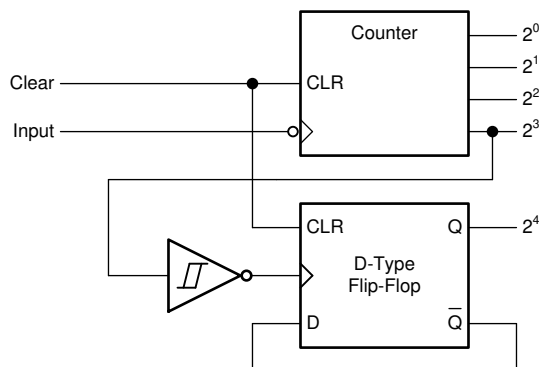


Figure 9-1. Typical Application Block Diagram

9.2.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LV14B-EP plus the maximum static supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LV14B-EP plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74LV14B-EP can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74LV14B-EP can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and Cpd Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.2 Input Considerations

Input signals must cross $V_{t-(min)}$ to be considered a logic LOW, and $V_{t+(max)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LV14B-EP (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k Ω resistor value is often used due to these factors.

The SN74LV14B-EP has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the $\Delta V_{T(min)}$ in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

9.2.4 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; it will, however, optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74LV14B-EP to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$, which will not violate the maximum output current from the *Absolute Maximum Ratings*. Most CMOS inputs have a resistive load measured in $M\Omega$; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

9.2.5 Application Curves

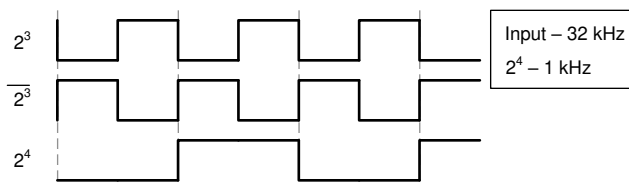


Figure 9-2. Application Timing Diagram

9.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Absolute Maximum Ratings* section. Each V_{CC} terminal must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, TI recommends a 0.1- μ F capacitor; if there are multiple V_{CC} terminals, then TI recommends a 0.01- μ F or 0.022- μ F capacitor for each power terminal. Multiple bypass capacitors can be paralleled to reject different frequencies of noise. Frequencies of 0.1 μ F and 1 μ F are commonly used in parallel. The bypass capacitor must be installed as close as possible to the power terminal for best results.

9.4 Layout

9.4.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

9.4.2 Layout Example

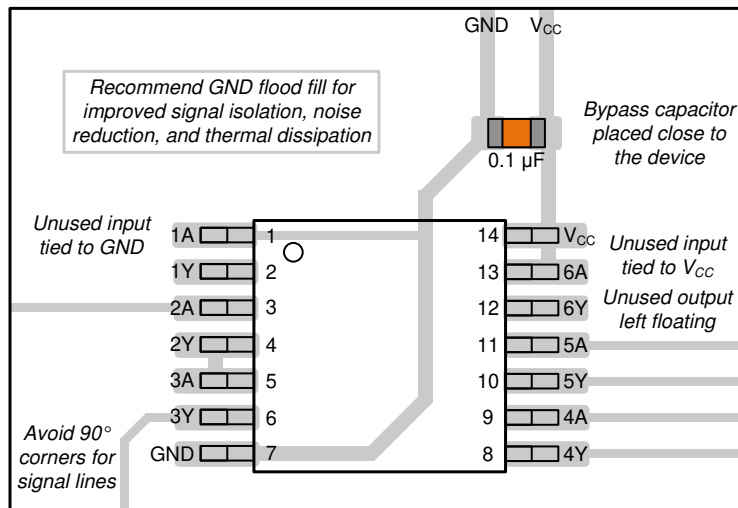


Figure 9-3. Layout Example for the SN74LV14B-EP in the PW Package

10 Device and Documentation Support

10.1 Documentation Support

10.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and Cpd Calculation](#)
- Texas Instruments, [Introduction to Logic](#)
- Texas Instruments, [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#)
- Texas Instruments, [Understanding Schmitt Triggers](#)

10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates—including silicon errata—go to the product folder for your device on [ti.com](#). In the upper right-hand corner, click the *Alert me* button. This registers you to receive a weekly digest of product information that has changed (if any). For change details, check the revision history of any revised document.

10.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

10.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
All trademarks are the property of their respective owners.

10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LV14BMPWREP	ACTIVE	TSSOP	PW	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	LV14BEP	Samples
V62/23623-01XE	ACTIVE	TSSOP	PW	14	3000	TBD	Call TI	Call TI			Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LV14BMPWREP	TSSOP	PW	14	3000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS

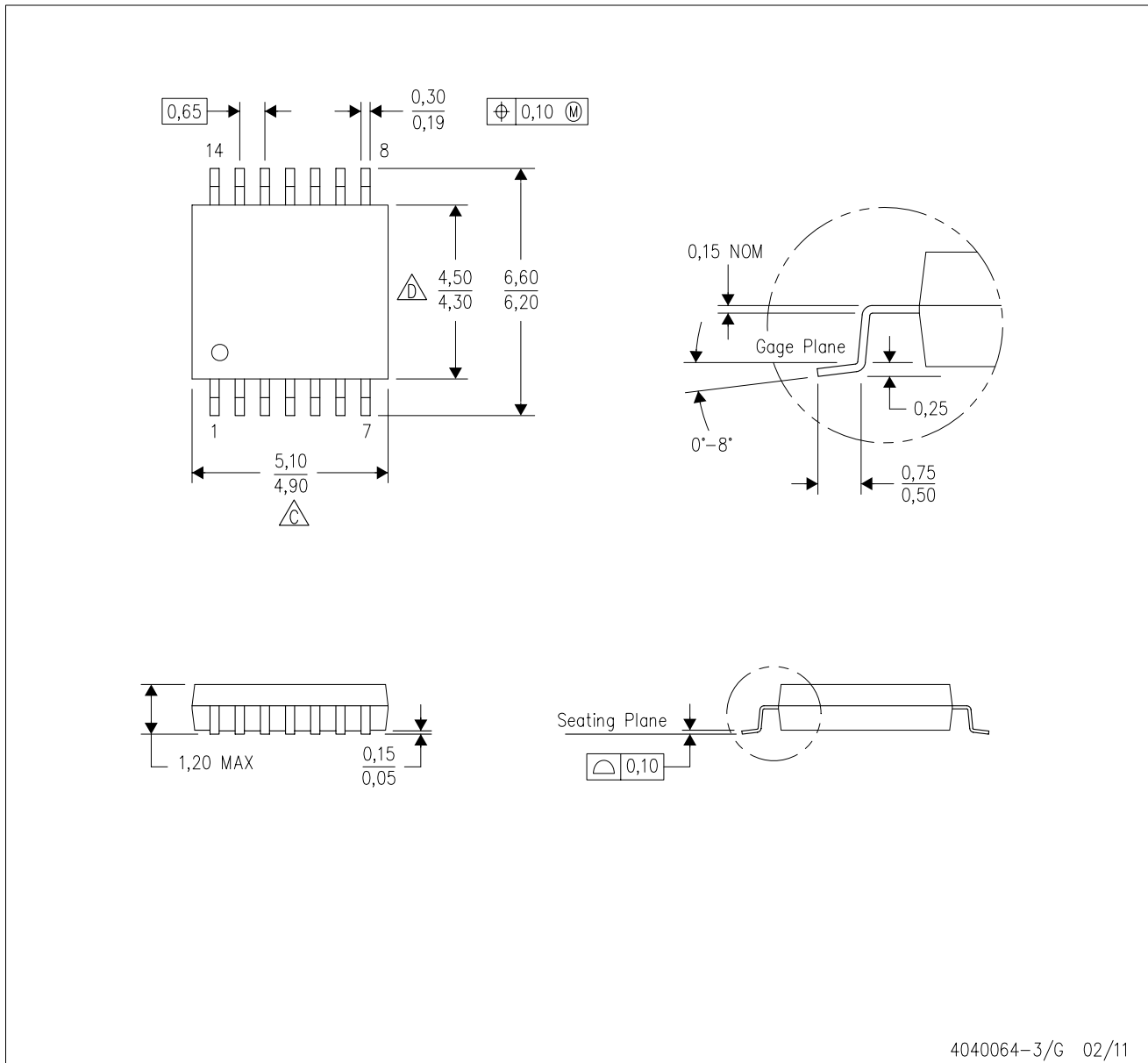

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LV14BMPWREP	TSSOP	PW	14	3000	356.0	356.0	35.0

MECHANICAL DATA

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
 - E. Falls within JEDEC MO-153

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